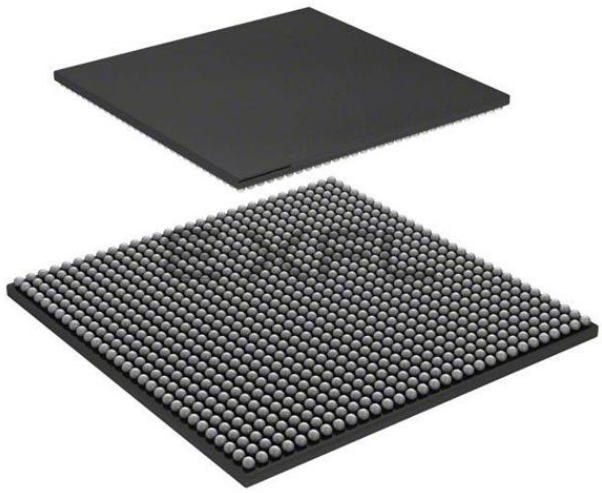

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Quad ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™, ARM Mali™-400 MP2
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 600MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 747K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	900-BBGA, FCBGA
Supplier Device Package	900-FCBGA (31x31)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu15eg-l2ffvc900e

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{CCO_PSDDR}	PS DDR I/O supply voltage.	–0.500	1.650	V
$V_{CC\_PSDDR\_PLL}$	PS DDR PLL supply voltage.	–0.500	2.000	V
V_{CCO_PSIO}	PS I/O supply.	–0.500	3.630	V
V_{PSIN}[2]	PS I/O input voltage.	–0.500	V_{CCO_PSIO} + 0.550	V
	PS DDR I/O input voltage.	–0.500	V_{CCO_PSDDR} + 0.550	V
V_{CC_PSBATT}	PS battery-backed RAM and battery-backed real-time clock (RTC) supply voltage.	–0.500	2.000	V
Programmable Logic (PL)				
V_{CCINT}	Internal supply voltage.	–0.500	1.000	V
V_{CCINT_IO}[3]	Internal supply voltage for the I/O banks.	–0.500	1.000	V
V_{CCAUX}	Auxiliary supply voltage.	–0.500	2.000	V
V_{CCBRAM}	Supply voltage for the block RAM memories.	–0.500	1.000	V
V_{CCO}	Output drivers supply voltage for HD I/O banks.	–0.500	3.400	V
	Output drivers supply voltage for HP I/O banks.	–0.500	2.000	V
V_{CCAUX_IO}[4]	Auxiliary supply voltage for the I/O banks.	–0.500	2.000	V
V_{REF}	Input reference voltage.	–0.500	2.000	V
V_{IN}[2][5][7]	I/O input voltage for HD I/O banks.[6]	–0.550	V_{CCO} + 0.550	V
	I/O input voltage for HP I/O banks.	–0.550	V_{CCO} + 0.550	V
I_{DC}	Available output current at the pad.	–20	20	mA
I_{RMS}	Available RMS output current at the pad.	–20	20	mA
GTH or GTY Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for transceiver circuits.	–0.500	1.000	V
$V_{MGTAVTT}$	Analog supply voltage for transceiver termination circuits.	–0.500	1.300	V
$V_{MGTVCCAUX}$	Auxiliary analog Quad PLL (QPLL) voltage supply for transceivers.	–0.500	1.900	V
$V_{MGTREFCLK}$	Transceiver reference clock absolute input voltage.	–0.500	1.300	V
$V_{MGTAVTTRCAL}$	Analog supply voltage for the resistor calibration circuit of the transceiver column.	–0.500	1.300	V
V_{IN}	Receiver (RXP/RXN) and transmitter (TXP/TXN) absolute input voltage.	–0.500	1.200	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating.[8]	–	10	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$.	–	10	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND.[9]	–	0	mA
$I_{DCIN-PROG}$	DC input current for receiver input pins DC coupled RX termination = programmable.[10]	–	0	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating.	–	6	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$.	–	6	mA

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.(12)	–	260	°C
T_j	Maximum junction temperature.(12)	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Table 2: **Recommended Operating Conditions(1)(2) *(Cont'd)***

Symbol	Description	Min	Typ	Max	Units
PL System Monitor					
V_{CCADC}	PL System Monitor supply relative to GNDADC.	1.746	1.800	1.854	V
V_{REFP}	PL System Monitor externally supplied reference voltage relative to GNDADC.	1.200	1.250	1.300	V
Temperature					
T_j(13)	Junction temperature operating range for extended (E) temperature devices.(14)	0	–	100	°C
	Junction temperature operating range for industrial (I) temperature devices.	–40	–	100	°C
	Junction temperature operating range for eFUSE programming.	–40	–	125	°C

Notes:

1. All voltages are relative to GND.
2. For the design of the power distribution system consult *UltraScale Architecture PCB Design Guide* (UG583).
3. $V_{CC\_PSINTFP\_DDR}$ must be tied to $V_{CC\_PSINTFP}$.
4. Includes V_{CCO_PSDDR} of 1.2V, 1.35V, 1.5V at ±5% and 1.1V +0.07V/–0.04V depending upon the tolerances required by specific memory standards.
5. Applies to all PS I/O supply banks. Includes V_{CCO_PSIO} of 1.8V, 2.5V, and 3.3V at ±5%.
6. If the battery-backed RAM or RTC is not used, connect V_{CC_PSBATT} to GND or V_{CC_PSAUX}. The V_{CC_PSAUX} maximum of 1.89V is acceptable on an unused V_{CC_PSBATT}.
7. V_{CCINT_IO} must be connected to V_{CCBRAM}.
8. Includes V_{CCO} of 1.0V (HP I/O only), 1.2V, 1.35V, 1.5V, 1.8V, 2.5V (HD I/O only) at ±5%, and 3.3V (HD I/O only) at +3/–5%.
9. V_{CCAUX_IO} must be connected to V_{CCAUX}.
10. The lower absolute voltage specification always applies.
11. A total of 200 mA per bank should not be exceeded.
12. Each voltage listed requires filtering as described in *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
13. Xilinx recommends measuring the Tj of a device using the system monitor as described in the *UltraScale Architecture System Monitor User Guide* (UG580). The SYSMON temperature measurement errors (that are described in Table 69 and Table 124) must be accounted for in your design. For example, when using the PL system monitor with an external reference of 1.25V, when SYSMON reports 97°C, there is a measurement error ±3°C. A reading of 97°C is considered the maximum adjusted Tj (100°C – 3°C = 97°C).
14. Devices labeled with the speed/temperature grade of -2LE normally operate under Extended (E) temperature grade specifications with a maximum junction temperature of 100°C. However, E temperature grade devices can operate for a limited time at a junction temperature of 110°C. Timing parameters adhere to the same speed file at 110°C as they do at 100°C, regardless of operating voltage (nominal voltage of 0.85V or a low-voltage of 0.72V). Operation at Tj = 110°C is limited to 1% of the device lifetime and can occur sequentially or at regular intervals as long as the total time does not exceed 1% of the device lifetime.

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* (DS890).

Table 3: **Available Speed Grades and Operating Voltages**

Speed Grade	V_{CCINT}	$V_{CC\_PSINTLP}$	$V_{CC\_PSINTFP}$	$V_{CC\_PSINTFP\_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ(1)	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).(2)	–	–	15	µA
C_{IN}(3)	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	–	–	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	–	–	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	–	–	1.8	mA

Table 4: **DC Characteristics Over Recommended Operating Conditions *(Cont'd)***

Symbol	Description	Min	Typ(1)	Max	Units
Differential termination	Programmable differential termination (TERM_100) for HP I/O banks.	–35%	100	+35%	Ω
n	Temperature diode ideality factor.	–	1.026	–	–
r	Temperature diode series resistance.	–	2	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. For HP I/O banks with a V_{CCO} of 1.8V and separated V_{CCO} and V_{CCAUX_IO} power supplies, the I_L maximum current is 70 µA.
3. This measurement represents the die capacitance at the pad, not including the package.
4. Maximum value specified for worst case process at 25°C.
5. I_{CC_PSBATT} is measured when the battery-backed RAM (BBRAM) is enabled.
6. Do not program eFUSE during device configuration (e.g., during configuration, during configuration readback, or when readback CRC is active).
7. If VRP resides at a different bank (DCI cascade), the range increases to ±15%.
8. VRP resistor tolerance is (240Ω ±1%)
9. On-die input termination resistance, for more information see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Table 5: **PS MIO Pull-up and Pull-down Current**

Symbol	Description	Min	Max	Units
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 3.3V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 2.5V.	20	80	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO_PSMIO} = 1.8V.	15	65	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 2.5V.	20	80	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	15	65	µA

V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot

Table 6: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HD I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	90%
V_{CCO} + 0.40	100%	–0.40	78%
V_{CCO} + 0.45	100%	–0.45	40%
V_{CCO} + 0.50	100%	–0.50	24%
V_{CCO} + 0.55	100%	–0.55	18.0%
V_{CCO} + 0.60	100%	–0.60	13.0%
V_{CCO} + 0.65	100%	–0.65	10.8%
V_{CCO} + 0.70	92%	–0.70	9.0%
V_{CCO} + 0.75	92%	–0.75	7.0%
V_{CCO} + 0.80	92%	–0.80	6.0%
V_{CCO} + 0.85	92%	–0.85	5.0%
V_{CCO} + 0.90	92%	–0.90	4.0%
V_{CCO} + 0.95	92%	–0.95	2.5%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 7: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HP I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO} + 0.30	100%	–0.30	100%
V_{CCO} + 0.35	100%	–0.35	100%
V_{CCO} + 0.40	92%	–0.40	92%
V_{CCO} + 0.45	50%	–0.45	50%
V_{CCO} + 0.50	20%	–0.50	20%
V_{CCO} + 0.55	10%	–0.55	10%
V_{CCO} + 0.60	6%	–0.60	6%
V_{CCO} + 0.65	2%	–0.65	2%
V_{CCO} + 0.70	2%	–0.70	2%

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. For UI smaller than 20 µs.

Table 8: **V_{PSIN} Maximum Allowed AC Voltage Overshoot and Undershoot for PS I/O Banks(1)**

AC Voltage Overshoot	% of UI at –40°C to 100°C	AC Voltage Undershoot	% of UI at –40°C to 100°C
V_{CCO_PSIO} + 0.30	100%	–0.30	100%
V_{CCO_PSIO} + 0.35	100%	–0.35	75%
V_{CCO_PSIO} + 0.40	100%	–0.40	45%
V_{CCO_PSIO} + 0.45	100%	–0.45	40%
V_{CCO_PSIO} + 0.50	75%	–0.50	10%
V_{CCO_PSIO} + 0.55	75%	–0.55	6%
V_{CCO_PSIO} + 0.60	60%	–0.60	2%
V_{CCO_PSIO} + 0.65	30%	–0.65	0%
V_{CCO_PSIO} + 0.70	20%	–0.70	0%
V_{CCO_PSIO} + 0.75	10%	–0.75	0%
V_{CCO_PSIO} + 0.80	10%	–0.80	0%
V_{CCO_PSIO} + 0.85	8%	–0.85	0%
V_{CCO_PSIO} + 0.90	6%	–0.90	0%
V_{CCO_PSIO} + 0.95	6%	–0.95	0%

Notes:

1. A total of 200 mA per bank should not be exceeded.

Power Supply Sequencing

PS Power-On/Off Power Supply Sequencing

The low-power domain (LPD) must operate before the full-power domain (FPD) can function. The low-power and full-power domains can be powered simultaneously. The PS_POR_B input must be asserted to GND during the power-on sequence (see Table 37). The FPD (when used) must be powered before PS_POR_B is released.

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the low-power domain (LPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTLP}$
2. V_{CC_PSAUX}, V_{CC_PSADC}, and V_{CC_PSPLL} in any order or simultaneously.
3. V_{CCO_PSIO}

To achieve minimum current draw and ensure that the I/Os are 3-stated at power-on, the recommended power-on sequence for the full-power domain (FPD) is listed. The recommended power-off sequence is the reverse of the power-on sequence.

1. $V_{CC\_PSINTFP}$ and $V_{CC\_PSINTFP\_DDR}$ driven from the same supply source.
2. $V_{PS\_MGTRAVCC}$ and $V_{CC\_PSDDR\_PLL}$ in any order or simultaneously.
3. $V_{PS\_MGTRAVTT}$ and V_{CCO_PSDDR} in any order or simultaneously.

PL Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCINT_IO}/V_{CCBRAM}/V_{CCINT_VCU}, V_{CCAUX}/V_{CCAUX_IO}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCINT_IO}/V_{CCBRAM} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCINT_IO} must be connected to V_{CCBRAM}. If V_{CCAUX}/V_{CCAUX_IO} and V_{CCO} have the same recommended voltage levels, they can be powered by the same supply and ramped simultaneously. V_{CCAUX} and V_{CCAUX_IO} must be connected together. V_{CCADC} and V_{REF} can be powered at any time and have no power-up sequencing requirements.

The recommended power-on sequence to achieve minimum current draw for the GTH or GTY transceivers is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTVCCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

Table 11: **Power Supply Ramp Time *(Cont'd)***

Symbol	Description	Min	Max	Units
T_{VCCO_PSDDR}	Ramp time from GND to 95% of V_{CCO_PSDDR}.	0.2	40	ms
$T_{VCC\_PSDDR\_PLL}$	Ramp time from GND to 95% of $V_{CC\_PSDDR\_PLL}$.	0.2	40	ms
T_{VCCO_PSIO}	Ramp time from GND to 95% of V_{CCO_PSIO}.	0.2	40	ms

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

PS I/O Levels

Table 12: **PS MIO and CONFIG DC Input and Output Levels(1)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
LVCMOS33	–0.300	0.800	2.000	V_{CCO_PSIO}	0.40	2.40	12	–12
LVCMOS25	–0.300	0.700	1.700	V_{CCO_PSIO} + 0.30	0.70	1.70	12	–12
LVCMOS18	–0.300	35% V_{CCO_PSIO}	65% V_{CCO_PSIO}	V_{CCO_PSIO} + 0.30	0.45	V_{CCO_PSIO} – 0.45	12	–12

Notes:
1. Tested according to relevant specifications.

Table 13: **PS DDR DC Input and Output Levels(1)**

DDR Standard	V_{IL}		V_{IH}		V_{OL}(2)	V_{OH}(2)	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
DDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.8 x V_{CCO_PSDDR} – 0.150	0.8 x V_{CCO_PSDDR} + 0.150	10	–0.1
LPDDR4	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.3 x V_{CCO_PSDDR} – 0.150	0.3 x V_{CCO_PSDDR} + 0.150	0.1	–10
DDR3	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.175	0.5 x V_{CCO_PSDDR} + 0.175	8	–8
LPDDR3	0.000	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8
DDR3L	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO_PSDDR}	0.5 x V_{CCO_PSDDR} – 0.150	0.5 x V_{CCO_PSDDR} + 0.150	8	–8

Notes:
1. Tested according to relevant specifications.
2. DDR4 V_{OL}/V_{OH} specifications are only applicable for DQ/DQS pins.

Table 15: **SelectIO DC Input and Output Levels for HP I/O Banks(1)(2)(3)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	5.8	–5.8
HSTL_I_12	–0.300	V_{REF} – 0.080	V_{REF} + 0.080	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	4.1	–4.1
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	6.2	–6.2
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVDCI_15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
LVDCI_18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	7.0	–7.0
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.0	–8.0
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	9.0	–9.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	10.0	–10.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	7.0	–7.0
MIPI_DPHY_DCI_LP(6)	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 16, Table 20, Table 21, and Table 22.
4. Supported drive strengths of 2, 4, 6, or 8 mA in HP I/O banks.
5. Supported drive strengths of 2, 4, 6, 8, or 12 mA in HP I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

Table 16: **DC Input Levels for Single-ended POD10 and POD12 I/O Standards(1)(2)**

I/O Standard	V_{IL}		V_{IH}	
	V, Min	V, Max	V, Min	V, Max
POD10	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300
POD12	–0.300	V_{REF} – 0.068	V_{REF} + 0.068	V_{CCO} + 0.300

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).

Processor System (PS) Performance Characteristics

Table 28: **Processor Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F_{APUMAX}	Maximum APU clock frequency.	1500	1333	1200	MHz
F_{RPUMAX}	Maximum RPU clock frequency.	600	533	500	MHz
F_{GPUMAX}	Maximum GPU clock frequency.	667	600	600	MHz

Table 29: **Configuration and Security Unit Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{CSUCIBMAX}$	Maximum CSU crypto interface block frequency.	400	400	400	MHz

Table 30: **PS DDR Performance**

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR4	All FFV packages, FBVB900, and SFVC784	Single rank component	664	2400	664	2400	664	2400	Mb/s
		1 rank DIMM(1)(2)	664	2133	664	2133	664	2133	Mb/s
		2 rank DIMM(1)(3)	664	1866	664	1866	664	1866	Mb/s
	SFVA625	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM(1)(2)	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM(1)(3)	664	1600	664	1600	664	1600	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
LPDDR4	All FFV packages, FBVB900 and SFVC784	Single die package(5)	664	2400	664	2400	664	2400	Mb/s
		Dual die package(4)(5)	664	2133	664	2133	664	2133	Mb/s
	SFVA625	Single die package(5)	664	2133	664	2133	664	2133	Mb/s
		Dual die package(4)(5)	664	1866	664	1866	664	1866	Mb/s
	SBVA484	Single die package(5)	664	1066	664	1066	664	1066	Mb/s
		Dual die package(4)(5)	664	1066	664	1066	664	1066	Mb/s

Table 45: **SD/SDIO Interface(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
$F_{SDSDRCLK2}$	SDR50 mode device clock frequency.	–	100	MHz
	SDR25 mode device clock frequency.	–	50	MHz
SD/SDIO Interface SDR12				
$T_{DCSDHSCLK3}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO3}$	Clock to output delay, all outputs.	1.0	36.8	ns
$T_{SDSDRDCK3}$	Input setup time, all inputs.	24.0	–	ns
$T_{SDSDRCKD3}$	Input hold time, all inputs.	1.5	–	ns
$F_{SDSDRCLK3}$	SDR12 mode device clock frequency.	–	25	MHz
SD/SDIO Interface High-Speed Mode				
$T_{DCSDHSCLK}$	SD device clock duty cycle.	47	53	%
$T_{SDHSCKO}$	Clock to output delay, all outputs.(2)	2.2	13.8	ns
$T_{SDHSDIVW}$	Input valid data window.(3)	0.35	–	UI
$F_{SDHSCLK}$	High-speed mode SD device clock frequency.	–	50	MHz
SD/SDIO Interface Standard Mode				
$T_{DCSDSCLK}$	SD device clock duty cycle.	45	55	%
T_{SDSCKO}	Clock to output delay, all outputs.	–2.0	4.5	ns
T_{SDSDCK}	Input setup time, all inputs.	2.0	–	ns
T_{SDSCKD}	Input hold time, all inputs.	2.0	–	ns
$F_{SDIDCLK}$	Clock frequency in identification mode.	–	400	KHz
F_{SDSCLK}	Standard SD device clock frequency.	–	19	MHz

Notes:

1. The test conditions SD/SDIO standard mode (default speed mode) use an 8 mA drive strength, fast slew rate, and a 30 pF load. For SD/SDIO high-speed mode, the test conditions use a 12 mA drive strength, fast slew rate, and a 30 pF load. For other SD/SDIO modes, the test conditions use a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. This specification is achieved using pre-determined DLL tuning.
3. This specification is required for capturing input data using DLL tuning.

PS I2C Controller Interface

Table 47: **I2C Interface(1)**

Symbol	Description	Min	Max	Units
I2C Fast-mode Interface				
$T_{I2CFCKL}$	SCL Low time.	1.3	–	µs
$T_{I2CFCKH}$	SCL High time.	0.6	–	µs
$T_{I2CFCKO}$	SDA clock to out delay.	–	900	ns
$T_{I2CFDCK}$	SDA input setup time.	100	–	ns
$F_{I2CFCLK}$	SCL clock frequency.	–	400	KHz
I2C Standard-mode Interface				
$T_{I2CSCKL}$	SCL Low time.	4.7	–	µs
$T_{I2CSCKH}$	SCL High time.	4.0	–	µs
$T_{I2CSCKO}$	SDA clock to out delay.	–	3450	ns
$T_{I2CSDCK}$	SDA input setup time.	250	–	ns
$F_{I2CSCLK}$	SCL clock frequency.	–	100	KHz

Notes:

1. The test conditions are configured to the LVCMOS 3.3V I/O standard with a 12 mA drive strength, fast slew rate, and a 15 pF load.

IOB High Performance (HP) Switching Characteristics

Table 76: **IOB High Performance (HP) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_12_F	0.394	0.394	0.402	0.394	0.402	0.423	0.423	0.443	0.423	0.443	0.553	0.553	0.582	0.553	0.582	ns
DIFF_HSTL_I_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSTL_I_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_HSTL_I_18_F	0.319	0.319	0.339	0.319	0.339	0.456	0.456	0.474	0.456	0.474	0.576	0.576	0.606	0.576	0.606	ns
DIFF_HSTL_I_18_M	0.319	0.319	0.339	0.319	0.339	0.570	0.570	0.603	0.570	0.603	0.653	0.653	0.692	0.653	0.692	ns
DIFF_HSTL_I_18_S	0.319	0.319	0.339	0.319	0.339	0.782	0.782	0.834	0.782	0.834	0.816	0.816	0.871	0.816	0.871	ns
DIFF_HSTL_I_DCI_12_F	0.394	0.394	0.402	0.394	0.402	0.406	0.406	0.429	0.406	0.429	0.534	0.534	0.564	0.534	0.564	ns
DIFF_HSTL_I_DCI_12_M	0.394	0.394	0.402	0.394	0.402	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSTL_I_DCI_12_S	0.394	0.394	0.402	0.394	0.402	0.755	0.755	0.806	0.755	0.806	0.842	0.842	0.907	0.842	0.907	ns
DIFF_HSTL_I_DCI_18_F	0.323	0.323	0.339	0.323	0.339	0.445	0.445	0.461	0.445	0.461	0.566	0.566	0.595	0.566	0.595	ns
DIFF_HSTL_I_DCI_18_M	0.323	0.323	0.339	0.323	0.339	0.555	0.555	0.586	0.555	0.586	0.643	0.643	0.684	0.643	0.684	ns
DIFF_HSTL_I_DCI_18_S	0.323	0.323	0.339	0.323	0.339	0.762	0.762	0.818	0.762	0.818	0.836	0.836	0.900	0.836	0.900	ns
DIFF_HSTL_I_DCI_F	0.397	0.397	0.417	0.397	0.417	0.431	0.431	0.445	0.431	0.445	0.555	0.555	0.575	0.555	0.575	ns
DIFF_HSTL_I_DCI_M	0.397	0.397	0.417	0.397	0.417	0.553	0.553	0.583	0.553	0.583	0.644	0.644	0.684	0.644	0.684	ns
DIFF_HSTL_I_DCI_S	0.397	0.397	0.417	0.397	0.417	0.767	0.767	0.823	0.767	0.823	0.848	0.848	0.912	0.848	0.912	ns
DIFF_HSTL_I_F	0.404	0.404	0.417	0.404	0.417	0.423	0.423	0.443	0.423	0.443	0.549	0.549	0.581	0.549	0.581	ns
DIFF_HSTL_I_M	0.404	0.404	0.417	0.404	0.417	0.555	0.555	0.586	0.555	0.586	0.640	0.640	0.677	0.640	0.677	ns
DIFF_HSTL_I_S	0.404	0.404	0.417	0.404	0.417	0.767	0.767	0.818	0.767	0.818	0.811	0.811	0.866	0.811	0.866	ns
DIFF_HSUL_12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_HSUL_12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.653	0.653	0.694	0.653	0.694	ns
DIFF_HSUL_12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.737	0.737	0.787	0.737	0.787	0.822	0.822	0.885	0.822	0.885	ns
DIFF_HSUL_12_F	0.394	0.394	0.402	0.394	0.402	0.412	0.412	0.430	0.412	0.430	0.538	0.538	0.566	0.538	0.566	ns
DIFF_HSUL_12_M	0.394	0.394	0.402	0.394	0.402	0.552	0.552	0.583	0.552	0.583	0.641	0.641	0.679	0.641	0.679	ns
DIFF_HSUL_12_S	0.394	0.394	0.402	0.394	0.402	0.752	0.752	0.800	0.752	0.800	0.813	0.813	0.868	0.813	0.868	ns
DIFF_POD10_DCI_F	0.411	0.411	0.430	0.411	0.430	0.425	0.425	0.444	0.425	0.444	0.555	0.555	0.584	0.555	0.584	ns
DIFF_POD10_DCI_M	0.411	0.411	0.430	0.411	0.430	0.542	0.542	0.571	0.542	0.571	0.640	0.640	0.681	0.640	0.681	ns
DIFF_POD10_DCI_S	0.411	0.411	0.430	0.411	0.430	0.754	0.754	0.815	0.754	0.815	0.850	0.850	0.917	0.850	0.917	ns
DIFF_POD10_F	0.411	0.411	0.433	0.411	0.433	0.438	0.438	0.459	0.438	0.459	0.569	0.569	0.601	0.569	0.601	ns
DIFF_POD10_M	0.411	0.411	0.433	0.411	0.433	0.538	0.538	0.568	0.538	0.568	0.630	0.630	0.667	0.630	0.667	ns
DIFF_POD10_S	0.411	0.411	0.433	0.411	0.433	0.766	0.766	0.821	0.766	0.821	0.836	0.836	0.894	0.836	0.894	ns
DIFF_POD12_DCI_F	0.407	0.407	0.432	0.407	0.432	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_POD12_DCI_M	0.407	0.407	0.432	0.407	0.432	0.543	0.543	0.572	0.543	0.572	0.638	0.638	0.678	0.638	0.678	ns
DIFF_POD12_DCI_S	0.407	0.407	0.432	0.407	0.432	0.772	0.772	0.822	0.772	0.822	0.862	0.862	0.929	0.862	0.929	ns
DIFF_POD12_F	0.409	0.409	0.430	0.409	0.430	0.455	0.455	0.476	0.455	0.476	0.595	0.595	0.626	0.595	0.626	ns
DIFF_POD12_M	0.409	0.409	0.430	0.409	0.430	0.551	0.551	0.582	0.551	0.582	0.641	0.641	0.679	0.641	0.679	ns
DIFF_POD12_S	0.409	0.409	0.430	0.409	0.430	0.767	0.767	0.817	0.767	0.817	0.832	0.832	0.889	0.832	0.889	ns
DIFF_SSTL12_DCI_F	0.381	0.381	0.400	0.381	0.400	0.425	0.425	0.443	0.425	0.443	0.558	0.558	0.586	0.558	0.586	ns
DIFF_SSTL12_DCI_M	0.381	0.381	0.400	0.381	0.400	0.557	0.557	0.587	0.557	0.587	0.654	0.654	0.694	0.654	0.694	ns
DIFF_SSTL12_DCI_S	0.381	0.381	0.400	0.381	0.400	0.754	0.754	0.803	0.754	0.803	0.842	0.842	0.908	0.842	0.908	ns

Table 79: **Output Delay Measurement Methodology**

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}[1] (pF)	V_{MEAS} (V)	V_{REF} (V)
LVCMOS, 1.2V	LVCMOS12	1M	0	0.6	0
LVCMOS, 1.5V	LVCMOS15	1M	0	0.75	0
LVCMOS, 1.8V	LVCMOS18	1M	0	0.9	0
LVCMOS, 2.5V	LVCMOS25	1M	0	1.25	0
LVCMOS, 3.3V	LVCMOS33	1M	0	1.65	0
LVTTL, 3.3V	LVTTL	1M	0	1.65	0
LVDCI, HSLVDCI, 1.5V	LVDCI_15, HSLVDCI_15	50	0	V_{REF}	0.75
LVDCI, HSLVDCI, 1.8V	LVDCI_15, HSLVDCI_18	50	0	V_{REF}	0.9
HSTL (high-speed transceiver logic), class I, 1.2V	HSTL_I_12	50	0	V_{REF}	0.6
HSTL, class I, 1.5V	HSTL_I	50	0	V_{REF}	0.75
HSTL, class I, 1.8V	HSTL_I_18	50	0	V_{REF}	0.9
HSUL (high-speed unterminated logic), 1.2V	HSUL_12	50	0	V_{REF}	0.6
SSTL12 (stub series terminated logic), 1.2V	SSTL12	50	0	V_{REF}	0.6
SSTL135 and SSTL135 class II, 1.35V	SSTL135, SSTL135_II	50	0	V_{REF}	0.675
SSTL15 and SSTL15 class II, 1.5V	SSTL15, SSTL15_II	50	0	V_{REF}	0.75
SSTL18, class I and class II, 1.8V	SSTL18_I, SSTL18_II	50	0	V_{REF}	0.9
POD10, 1.0V	POD10	50	0	V_{REF}	1.0
POD12, 1.2V	POD12	50	0	V_{REF}	1.2
DIFF_HSTL, class I, 1.2V	DIFF_HSTL_I_12	50	0	V_{REF}	0.6
DIFF_HSTL, class I, 1.5V	DIFF_HSTL_I	50	0	V_{REF}	0.75
DIFF_HSTL, class I, 1.8V	DIFF_HSTL_I_18	50	0	V_{REF}	0.9
DIFF_HSUL, 1.2V	DIFF_HSUL_12	50	0	V_{REF}	0.6
DIFF_SSTL12, 1.2V	DIFF_SSTL12	50	0	V_{REF}	0.6
DIFF_SSTL135 and DIFF_SSTL135 class II, 1.35V	DIFF_SSTL135, DIFF_SSTL135_II	50	0	V_{REF}	0.675
DIFF_SSTL15 and DIFF_SSTL15 class II, 1.5V	DIFF_SSTL15, DIFF_SSTL15_II	50	0	V_{REF}	0.75
DIFF_SSTL18, class I and II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	50	0	V_{REF}	0.9
DIFF_POD10, 1.0V	DIFF_POD10	50	0	V_{REF}	1.0
DIFF_POD12, 1.2V	DIFF_POD12	50	0	V_{REF}	1.2
LVDS (low-voltage differential signaling), 1.8V	LVDS	100	0	0[2]	0
SUB_LVDS, 1.8V	SUB_LVDS	100	0	0[2]	0
MIPI D-PHY (high speed) 1.2V	MIPI_DPHY_DCI_HS	100	0	0[2]	0
MIPI D-PHY (low power) 1.2V	MIPI_DPHY_DCI_LP	1M	0	0.6	0

Notes:

1. C_{REF} is the capacitance of the probe, nominally 0 pF.
2. The value given is the differential output voltage.

Device Pin-to-Pin Input Parameter Guidelines

The pin-to-pin numbers in Table 90 and Table 91 are based on the clock root placement in the center of the device. The actual pin-to-pin values will vary if the root placement selected is different. Consult the Vivado Design Suite timing report for the actual pin-to-pin values.

Table 90: **Global Clock Input Setup and Hold With 3.3V HD I/O without MMCM**

Symbol	Description		Device	Speed Grade and V_{CCINT} Operating Voltages					Units
				0.90V	0.85V		0.72V		
				-3	-2	-1	-2	-1	
Input Setup and Hold Time Relative to Global Clock Input Signal using SSTL15 Standard.(1)(2)(3)									
T_{PSFD_ZU2}	Global clock input and input flip-flop (or latch) without MMCM.	Setup	XCZU2	N/A	2.27	2.37	2.55	2.64	ns
T_{PHFD_ZU2}		Hold			–0.36	–0.36	–0.14	–0.14	ns
T_{PSFD_ZU3}		Setup	XCZU3	N/A	2.27	2.37	2.55	2.64	ns
T_{PHFD_ZU3}		Hold			–0.36	–0.36	–0.14	–0.14	ns
T_{PSFD_ZU4}		Setup	XCZU4	1.28	2.01	2.07	2.59	2.59	ns
T_{PHFD_ZU4}		Hold		–0.28	–0.28	–0.28	–0.09	–0.09	ns
T_{PSFD_ZU5}		Setup	XCZU5	1.28	2.01	2.07	2.59	2.59	ns
T_{PHFD_ZU5}		Hold		–0.28	–0.28	–0.28	–0.09	–0.09	ns
T_{PSFD_ZU6}		Setup	XCZU6	0.96	1.79	1.86	1.93	2.02	ns
T_{PHFD_ZU6}		Hold		–0.05	–0.05	–0.05	0.27	0.42	ns
T_{PSFD_ZU7}		Setup	XCZU7	1.43	2.32	2.42	2.60	2.69	ns
T_{PHFD_ZU7}		Hold		–0.40	–0.40	–0.40	–0.21	–0.21	ns
T_{PSFD_ZU9}		Setup	XCZU9	0.96	1.79	1.86	1.93	2.02	ns
T_{PHFD_ZU9}		Hold		–0.05	–0.05	–0.05	0.27	0.42	ns
T_{PSFD_ZU11}		Setup	XCZU11	1.28	2.01	2.07	2.59	2.59	ns
T_{PHFD_ZU11}		Hold		–0.29	–0.29	–0.29	–0.09	0.19	ns
T_{PSFD_ZU15}		Setup	XCZU15	0.96	1.79	1.85	1.92	2.01	ns
T_{PHFD_ZU15}		Hold		–0.04	–0.04	–0.04	0.27	0.43	ns
T_{PSFD_ZU17}		Setup	XCZU17	1.41	2.29	2.38	2.57	2.65	ns
T_{PHFD_ZU17}		Hold		–0.38	–0.38	–0.38	–0.19	–0.19	ns
T_{PSFD_ZU19}		Setup	XCZU19	1.41	2.29	2.38	2.57	2.65	ns
T_{PHFD_ZU19}		Hold		–0.38	–0.38	–0.38	–0.19	–0.19	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, slowest temperature, and slowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, fastest temperature, and fastest voltage.
2. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 103: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHTX}	Serial data rate range		0.500	–	F_{GTHMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.0}$	Total jitter(3)(4)	4.0 Gb/s	–	–	0.32	UI
$D_{J4.0}$	Deterministic jitter(3)(4)		–	–	0.16	UI
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI

Integrated Interface Block for Interlaken

More information and documentation on solutions using the integrated interface block for Interlaken can be found at UltraScale+ Interlaken. The *UltraScale Architecture and Product Overview* (DS890) lists how many blocks are in each Zynq UltraScale+ MPSoC. This section describes the following Interlaken configurations.

- 12 x 12.5 Gb/s protocol and lane logic mode (Table 118).
- 6 x 25.78125 Gb/s and 6 x 28.21 Gb/s protocol and lane logic mode (Table 119).
- 12 x 25.78125 Gb/s lane logic only mode (Table 120).

Zynq UltraScale+ MPSoCs in the SFVB784, FFVA676, and FFVA1156 packages are only supported using the 12 x 12.5 Gb/s Interlaken configuration. See Table 109 for the F_{GTYMAX} description.

Table 118: **Maximum Performance for Interlaken 12 x 12.5 Gb/s Protocol and Lane Logic Mode Designs**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
$F_{RX\_SERDES\_CLK}$	Receive serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
$F_{TX\_SERDES\_CLK}$	Transmit serializer/ deserializer clock	195.32		195.32		195.32		195.32		195.32		MHz
F_{DRP_CLK}	Dynamic reconfiguration port clock	250.00		250.00		250.00		250.00		250.00		MHz
		Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	Min(1)	Max	
F_{CORE_CLK}	Interlaken core clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz
F_{LBUS_CLK}	Interlaken local bus clock	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	300.00	322.27	MHz

Notes:

1. These are the minimum clock frequencies at the maximum lane performance.

Revision History

The following table shows the revision history for this document.

Date	Version	Description of Revisions
04/20/2017	1.3	Updated Table 25, Table 26, and Table 27 to production release for the following devices/speed/temperature grades in Vivado Design Suite 2017.1. XCZU2CG and XCZU2EG: –2E, -2I, -1E, -1I XCZU3CG and XCZU3EG: –2E, -2I, -1E, -1I XCZU6CG and XCZU6EG: –2E, -2I, -1E, -1I XCZU9CG and XCZU9EG: –2E, -2I, -1E, -1I Added -2E (V_{CCINT} = 0.85V) speed grade where applicable. Removed -3E speed grade from the XCZU2 and XCZU3 devices in Table 26 and where applicable. In Table 1, updated values and Note 2. In Table 2, added or updated many of the notes. Updated Table 4 including the notes and added Note 6. Moved and updated Table 5. Added Table 8. Updated Table 9 and added Note 4. Updated Table 10 and added Note 1. Revised V_{ICM} in Table 23. Updated Table 30 and removed Note 1. Added Table 31 and Table 32. Updated Table 33 and removed F_{FTMCLK}. Updated $T_{RFPSCLK}$ in Table 34. Updated Note 1 in Table 37. Updated Table 39. Removed the *PS NAND Memory Controller Interface* section. Significant changes to Table 41 and removed Note 3. Significant changes to Table 42 and updated Note 1. Removed $F_{TSU\_REF\_CLK}$ from Table 44. Revised Table 45 and added Note 2 and Note 3. Revised Table 46 and added Note 2 and Note 3. Updated Table 48. Updated Table 51 and removed Note 2. Revised Table 52. Revised many of the tables in the PS-GTR Transceiver section. Revised Table 70 and Table 71. Removed Note 8 from Table 74. Updated the values in Table 75, Table 76, Table 77, Table 80, Table 87, Table 88, Table 89, Table 90,and Table 91 to the Vivado Design Suite 2017.1 speed specifications. Updated the values in Table 81 and Table 82. Added values to Table 92. Updated Table 93. Revised D_{VPPOUT} in Table 94. Update the values in Table 96. Added Note 6 to Table 102. Updated Table 103 and Table 104. Revised D_{VPPOUT} in Table 106. Updated the values in Table 108. In Table 109 updated the -1 (0.85V) specifications and removed Note 1. In Table 114 updated the -1 (0.85V) specifications and added Note 6. In Table 115 and Table 116, added the 28.21 jitter tolerance values and revised the notes. Revised the Integrated Interface Block for Interlaken and Integrated Interface Block for 100G Ethernet MAC and PCS sections. Revised the Configuration Switching Characteristics section. Removed the *eFUSE Programming Conditions* table and added the specifications to Table 2 and Table 3.

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